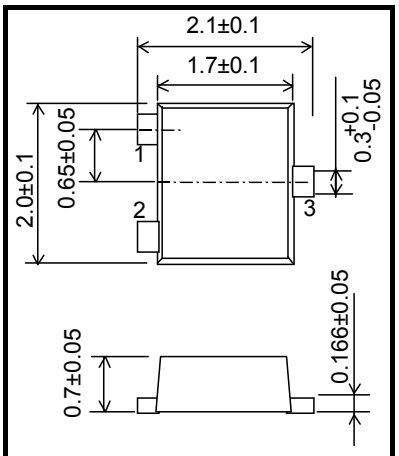
TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type

SSM3K122TU

Power Management Switch Applications
High-Speed Switching Applications

- 1.5 V drive
- Low ON-resistance: R_{on} = 304 mΩ (max) (@V_{GS} = 1.5 V)
  R_{on} = 211 mΩ (max) (@V_{GS} = 1.8 V)
  R_{on} = 161 mΩ (max) (@V_{GS} = 2.5 V)
  R_{on} = 123 mΩ (max) (@V_{GS} = 4.0 V)

Unit: mm



1: Gate
2: Source
3: Drain

UFM	
JEDEC	—
JEITA	—
TOSHIBA	2-2U1A

Weight: 6.6 mg (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DSS}	20	V
Gate-Source voltage		V_{GSS}	± 10	V
Drain current	DC	I_D	2.0	A
	Pulse	I_{DP}	4.0	
Drain power dissipation		$P_{D\ (Note\ 1)}$	800	mW
		$P_{D\ (Note\ 2)}$	500	
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on a ceramic board.
(25.4 mm × 25.4 mm × 0.8 t, Cu Pad: 645 mm^2)

Note 2: Mounted on a FR4 board.
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 645 mm^2)

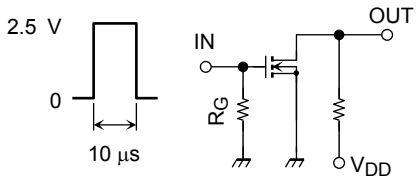
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition		Min	Typ.	Max	Unit
Drain-Source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 1 mA, V_{GS} = 0 V		20	—	—	V
		$V_{(BR)\ DSX}$	I_D = 1 mA, V_{GS} = − 10 V		12	—	—	
Drain cutoff current		I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V		—	—	1	μA
Gate leakage current		I_{GSS}	V_{GS} = ± 10 V, V_{DS} = 0 V		—	—	±1	μA
Gate threshold voltage		V_{th}	V_{DS} = 3 V, I_D = 1 mA		0.35	—	1.0	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 1.0 A	(Note 3)	2.6	5.2	—	S
Drain-Source ON-resistance		$R_{DS\ (ON)}$	I_D = 1.0 A, V_{GS} = 4.0 V	(Note 3)	—	87	123	mΩ
			I_D = 1.0 A, V_{GS} = 2.5 V	(Note 3)	—	112	161	
			I_D = 0.5 A, V_{GS} = 1.8 V	(Note 3)	—	147	211	
			I_D = 0.3 A, V_{GS} = 1.5 V	(Note 3)	—	182	304	
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz		—	195	—	pF
Output capacitance		C_{oss}			—	35	—	
Reverse transfer capacitance		C_{rss}			—	29	—	
Total Gate Charge		Q_g	V_{DS} = 10 V, I_D= 2.0 A, V_{GS} = 4 V		—	3.4	—	nC
Gate−Source Charge		Q_{gs}			—	2.3	—	
Gate−Drain Charge		Q_{gd}			—	1.1	—	
Switching time	Turn-on time	t_{on}	V_{DD} = 10 V, I_D = 0.5 A, V_{GS} = 0 to 2.5 V, R_G = 4.7 Ω		—	8.0	—	ns
	Turn-off time	t_{off}			—	9.0	—	
Drain-Source forward voltage		V_{DSF}	I_D = −2.0 A, V_{GS} = 0 V	(Note 3)	—	−0.85	-1.2	V

Note 3: Pulse test

Switching Time Test Circuit

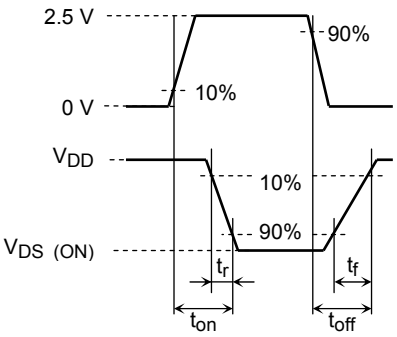
(a) Test Circuit



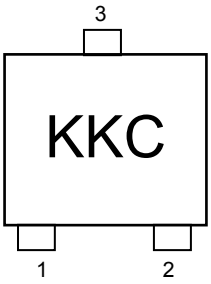
V_{DD} = 10 V
R_G = 4.7 Ω
D.U. ≦ 1%
V_{IN}: t_r, t_f < 5 ns
Common Source
Ta = 25°C

(b) V_{IN}

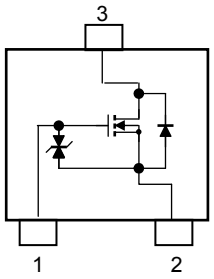
(c) V_{OUT}



Marking



Equivalent Circuit (top view)



Notice on Usage

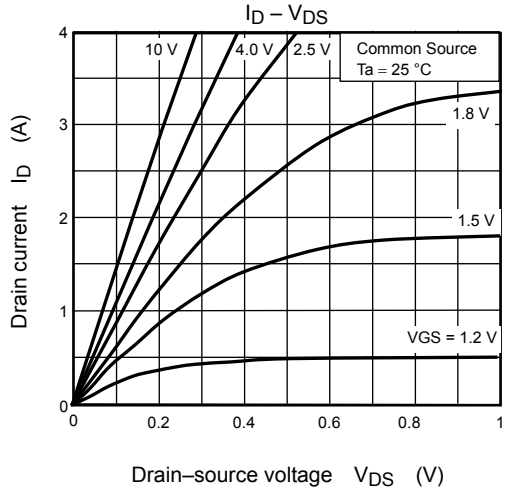
V_{th} can be expressed as the voltage between gate and source when the low operating current value is I_D = 1 mA for this product. For normal switching operation, $V_{GS\ (on)}$ requires a higher voltage than V_{th}, and $V_{GS\ (off)}$ requires a lower voltage than V_{th}. (The relationship can be established as follows: $V_{GS\ (off)} < V_{th} < V_{GS\ (on)}$.)

Take this into consideration when using the device.

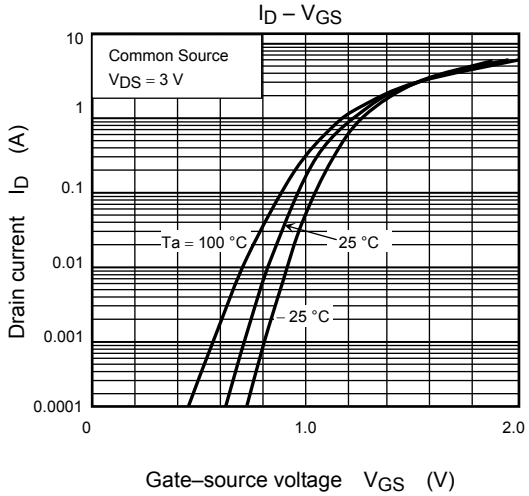
Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

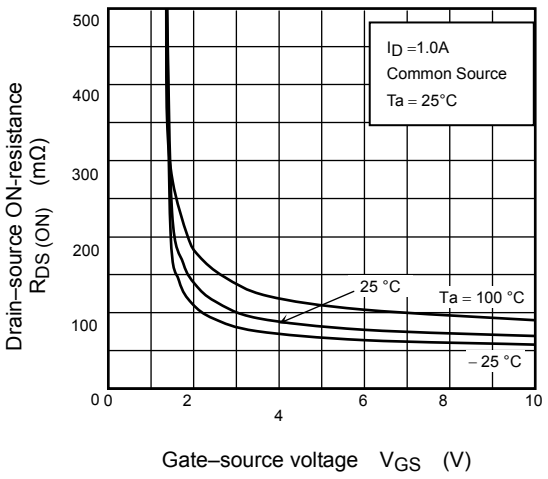
$I_D - V_{DS}$



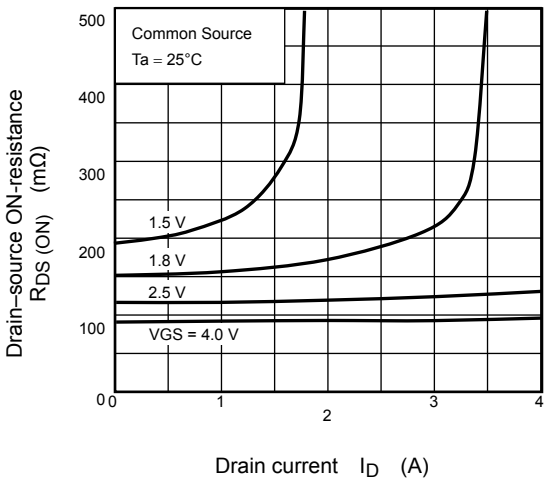
$I_D - V_{GS}$



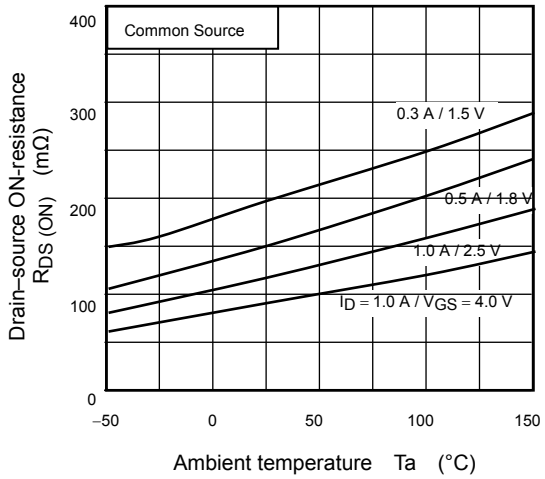
$R_{DS\ (ON)} - V_{GS}$



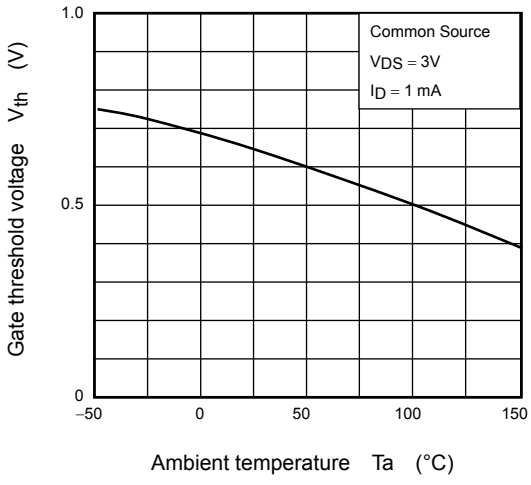
$R_{DS\ (ON)} - I_D$

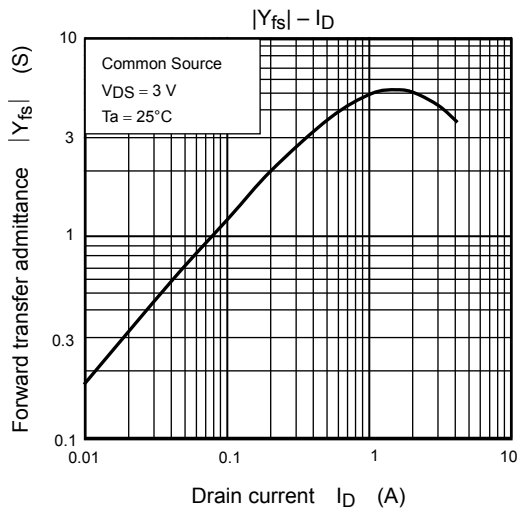


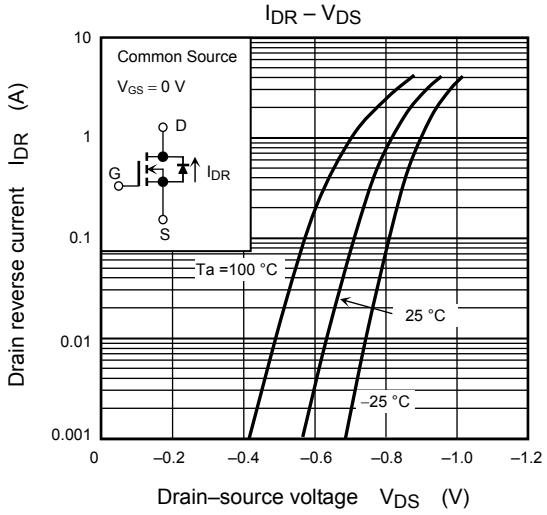
$R_{DS\ (ON)} - Ta$

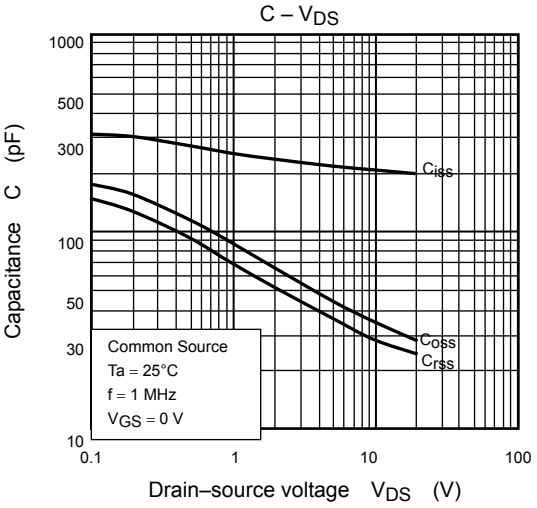


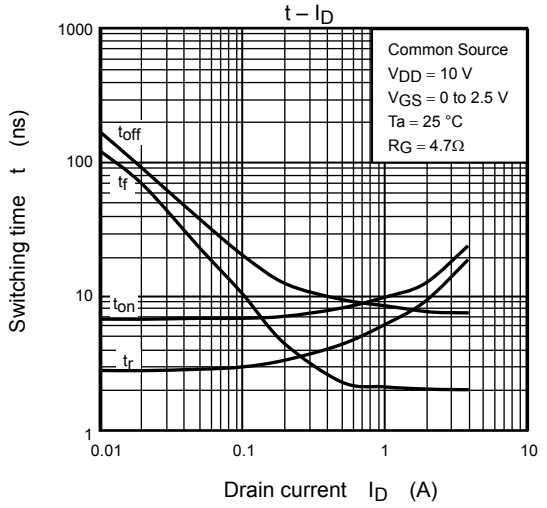
$V_{th} - Ta$

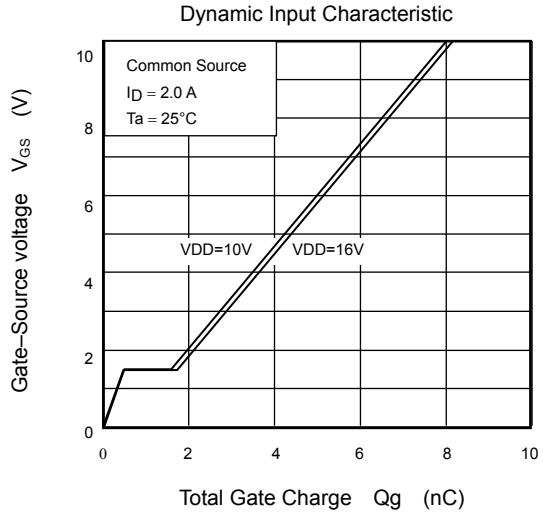



|Yfs| – ID
Common Source
VDS = 3 V
Ta = 25°C
Forward transfer admittance |Yfs| (S)
Drain current ID (A)
10
3
1
0.3
0.1
0.01
0.1
1
10

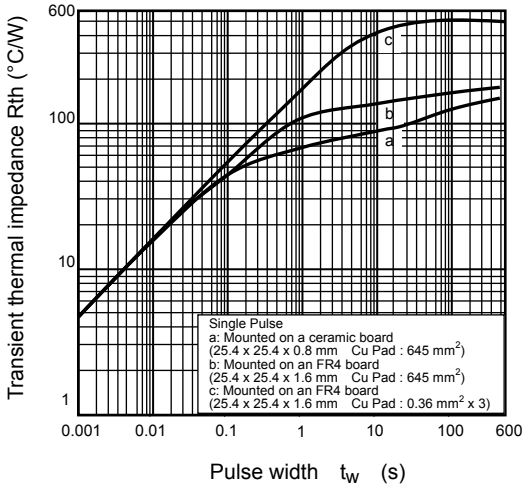

IDR – VDS
Common Source
VGS = 0 V
D
G
S
IDR
Ta =100 °C
25 °C
−25 °C
Drain reverse current IDR (A)
Drain–source voltage VDS (V)
10
1
0.1
0.01
0.001
0
−0.2
−0.4
−0.6
−0.8
−1.0
−1.2


C – VDS
Common Source
Ta = 25°C
f = 1 MHz
VGS = 0 V
Ciss
Coss
Crss
Capacitance C (pF)
Drain–source voltage VDS (V)
1000
500
300
100
50
30
10
0.1
1
10
100

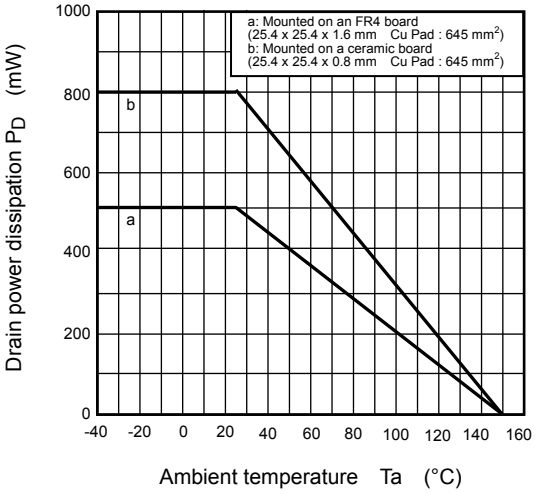

t – ID
Common Source
VDD = 10 V
VGS = 0 to 2.5 V
Ta = 25 °C
RG = 4.7Ω
toff
tf
ton
tr
Switching time t (ns)
Drain current ID (A)
1000
100
10
1
0.01
0.1
1
10


Dynamic Input Characteristic
Common Source
ID = 2.0 A
Ta = 25°C
VDD=10V
VDD=16V
Gate–Source voltage VGS (V)
Total Gate Charge Qg (nC)
10
8
6
4
2
0
0
2
4
6
8
10

$t - I_D$


Transient thermal impedance Rth (°C/W)
600
100
10
1
0.001
0.01
0.1
1
10
100
600
c
b
a
Single Pulse
a: Mounted on a ceramic board
(25.4 x 25.4 x 0.8 mm Cu Pad : 645 mm²)
b: Mounted on an FR4 board
(25.4 x 25.4 x 1.6 mm Cu Pad : 645 mm²)
c: Mounted on an FR4 board
(25.4 x 25.4 x 1.6 mm Cu Pad : 0.36 mm² x 3)
Pulse width t_w (s)

$P_D - T_a$


Drain power dissipation P_D (mW)
1000
800
600
400
200
0
-40
-20
0
20
40
60
80
100
120
140
160
a: Mounted on an FR4 board
(25.4 x 25.4 x 1.6 mm Cu Pad : 645 mm²)
b: Mounted on a ceramic board
(25.4 x 25.4 x 0.8 mm Cu Pad : 645 mm²)
b
a
Ambient temperature Ta (°C)

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